ARCHIVE INFORMATION

The RF Line NPN Silicon RF Power Transistor

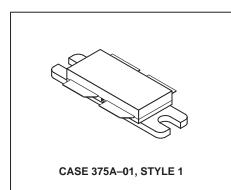
Designed for 26 Volt UHF large–signal, common emitter, Class AB linear amplifier applications in industrial and commercial FM/AM equipment operating in the range 800–960 MHz.

Specified 26 Volt, 900 MHz Characteristics
 Output Power = 150 Watts (PEP)
 Minimum Gain = 8.0 dB @ 900 MHz, Class AB
 Minimum Efficiency = 35% @ 900 MHz, 150 Watts (PEP)
 Maximum Intermodulation Distortion –28 dBc @ 150 Watts (PEP)

- Characterized with Series Equivalent Large—Signal Parameters from 800 to 960 MHz
- Silicon Nitride Passivated
- 100% Tested for Load Mismatch Stress at all Phase Angles with 5:1 VSWR
 26 Vdc, and Rated Output Power
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF899

150 W, 900 MHz RF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|------------------|-------------|---------------|
| Collector–Emitter Voltage | V _{CEO} | 28 | Vdc |
| Collector–Emitter Voltage | V _{CES} | 60 | Vdc |
| Emitter–Base Voltage | V _{EBO} | 4.0 | Vdc |
| Collector–Current — Continuous | I _C | 25 | Adc |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 230 1.33 | Watts W/°C |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|-----------------|------|------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 0.75 | °C/W |

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

| , , | • | | | | | |
|---|----------------------|-----|-----|-----|------|--|
| Characteristic | Symbol | Min | Тур | Max | Unit | |
| OFF CHARACTERISTICS | | | | | | |
| Collector–Emitter Breakdown Voltage (I _C = 100 mAdc, I _B = 0) | V _{(BR)CEO} | 28 | 37 | _ | Vdc | |
| Collector–Emitter Breakdown Voltage (I _C = 50 mAdc, V _{BE} = 0) | V _{(BR)CES} | 60 | 85 | _ | Vdc | |
| Emitter–Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0) | V _{(BR)EBO} | 4.0 | 4.9 | _ | Vdc | |
| Collector Cutoff Current (V _{CE} = 30 Vdc, V _{BE} = 0) | I _{CES} | _ | _ | 10 | mAdc | |
| ON CHARACTERISTICS | | | • | • | • | |
| DC Current Gain (I _{CE} = 1.0 Adc, V _{CE} = 5.0 Vdc) | h _{FE} | 30 | 75 | 120 | _ | |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Output Capacitance (V _{CB} = 26 Vdc, I _E = 0, f = 1.0 MHz) (1) | C _{ob} | _ | 75 | _ | pF | |
| | | | • | | | |

(1) For information only. This part is collector matched.

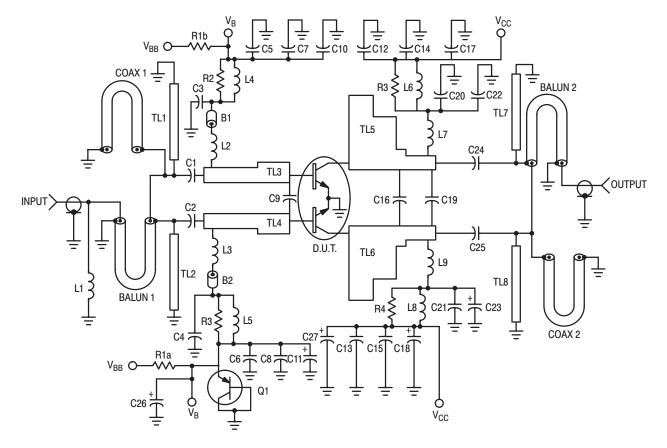
(continued)





ELECTRICAL CHARACTERISTICS — **continued** (T_C = 25°C unless otherwise noted.)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|-----------------|---|-----|-----|------|
| FUNCTIONAL CHARACTERISTICS | | | | | |
| Common–Emitter Amplifier Power Gain V_{CC} = 26 Vdc, P_{out} = 150 Watts (PEP), I_{cq} = 300 mA, f_1 = 900 MHz, f_2 = 900.1 MHz | G _{pe} | 8.0 | 9.0 | _ | dB |
| Collector Efficiency V_{CC} = 26 Vdc, P_{out} = 150 Watts (PEP), I_{cq} = 300 mA, f_1 = 900 MHz, f_2 = 900.1 MHz | η | 30 | 40 | _ | % |
| 3rd Order Intermodulation Distortion $V_{CC} = 26 \text{ Vdc}, P_{out} = 150 \text{ Watts (PEP)}, I_{cq} = 300 \text{ mA}, f_1 = 900 \text{ MHz}, \\ f_2 = 900.1 \text{ MHz}$ | IMD | _ | -32 | -28 | dBc |
| Output Mismatch Stress V_{CC} = 26 Vdc, P_{out} = 150 Watts (PEP), I_{cq} = 300 mA, f_1 = 900 MHz, f_2 = 900.1 MHz, VSWR = 5:1 (all phase angles) | Ψ | No Degradation in Output Power Before and After Test | | | |



B1, B2 — Ferrite Bead, Ferroxcube #56–590–65–3B C1, C2, C24, C25 — 43 pF, B Case, ATC Chip Capacitor C3, C4, C20, C21 — 100 pF, B Case, ATC Chip Capacitor C5, C6, C12, C13 — 1000 pF, B Case, ATC Chip Capacitor C7, C8, C14, C15 — 1800 pF, AVX Chip Capacitor C9 — 9.1 pF, A Case, ATC Chip Capacitor C10, C11, C17, C18, C22, C23 — 10 μF , Electrolytic Capacitor

Panasonic

 ${
m C16-3.9~pF}$, B Case, ATC Chip Capacitor ${
m C19-0.8~pF}$, B Case, ATC Chip Capacitor

C26 — 200 μF, Electrolytic Capacitor Mallory Sprague

C27 — 500 µF Electrolytic Capacitor

L1 — 5 Turns 24 AWG IDIA 0.059" Choke, 19.8 nH L2, L3, L7, L9 — 4 Turns 20 AWG IDIA 0.163" Choke L4, L5, L6, L8 — 12 Turns 22 AWG IDIA 0.140" Choke N1, N2 — Type N Flange Mount, Omni Spectra Q1 — Bias Transistor BD136 PNP R2, R3, R4, R5 — 4.0 x 39 Ohm 1/8 W Chips in Parallel R1a, R1b — 56 Ohm 1.0 W TL1–TL8 — See Photomaster Balun1, Balun2, Coax 1, Coax 2 — 2.20" 50 Ohm 0.088" o.d. Semi–rigid Coax, Micro Coax Board — 1/32" Glass Teflon, $\varepsilon_{\rm r}$ = 2.55" Arlon (GX–0300–55–22)

Figure 1. 900 MHz Power Gain Test Circuit

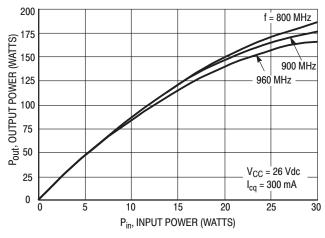


Figure 2. Output Power versus Input Power

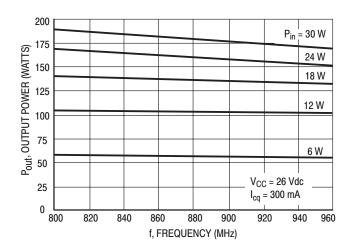


Figure 3. Output Power versus Frequency

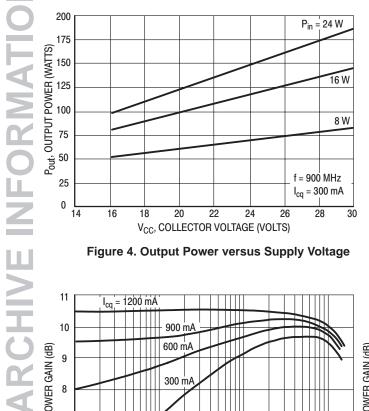


Figure 4. Output Power versus Supply Voltage

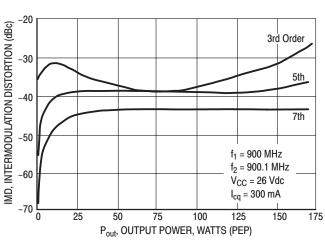


Figure 5. Intermodulation versus Output Power

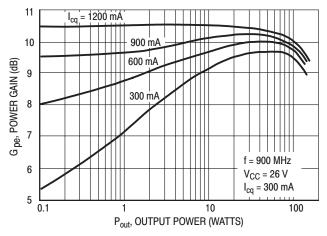


Figure 6. Power Gain versus Output Power

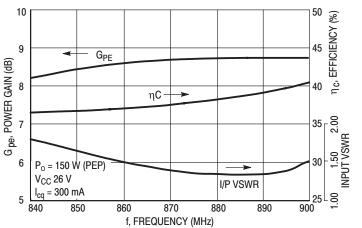
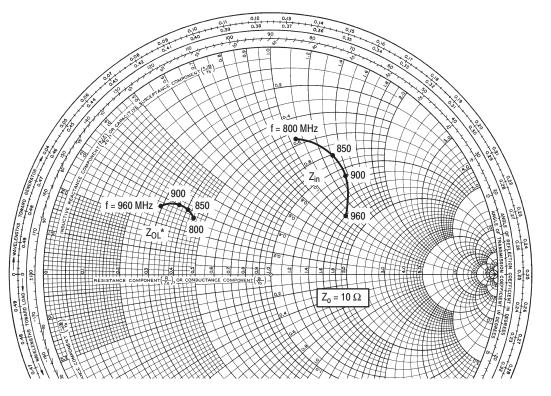


Figure 7. Broadband Test Fixture Performance

MOTOROLA RF DEVICE DATA MRF899



| f MHz | Z _{in} Ohms | Z _{OL} * Ohms |
|----------|-------------------------|---------------------------|
| 800 | 5.51 + j10.6 | 4.52 + j2.64 |
| 850 | 8.17 + j13.2 | 4.21 + j2.98 |
| 900 | 11.2 + j13.8 | 3.68 + j2.97 |
| 960 | 16.8 + j10.1 | 2.98 + j2.71 |

Z_{OL}* = Conjugate of optimum load impedance into which the device operates at a given output power, voltage and frequency.

NOTE: Z_{in} & Z_{OL}* are given from base–to–base and collector–to–collector respectively

Figure 8. Input and Output Impedances with Circuit Tuned for Maximum Gain @ P_0 = 150 W (PEP), V_{CC} = 26 V

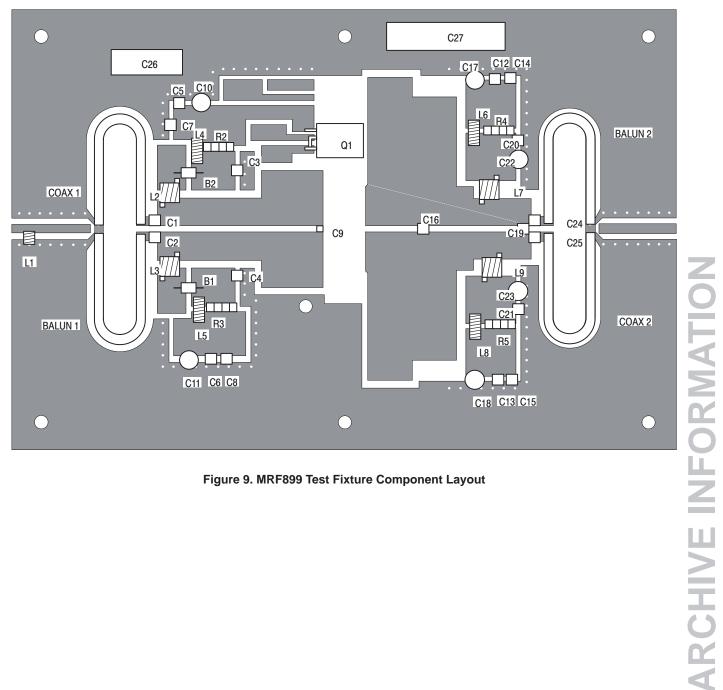
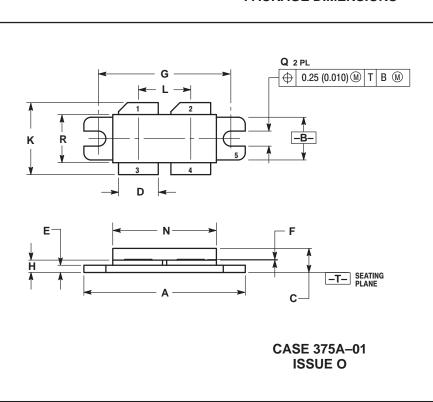


Figure 9. MRF899 Test Fixture Component Layout

MOTOROLA RF DEVICE DATA MRF899



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-----------|-----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.330 | 1.350 | 33.79 | 34.29 |
| В | 0.375 | 0.395 | 9.52 | 10.03 |
| C | 0.180 | 0.205 | 4.57 | 5.21 |
| D | 0.320 | 0.340 | 8.13 | 8.64 |
| Е | 0.060 | 0.070 | 1.52 | 1.77 |
| F | 0.004 | 0.006 | 0.11 | 0.15 |
| G | 1.100 | BSC | 27.94 BSC | |
| Н | 0.082 | 0.097 | 2.08 | 2.46 |
| K | 0.580 | 0.620 | 14.73 | 15.75 |
| L | 0.435 | 0.435 BSC | | BSC |
| N | 0.845 | 0.875 | 21.46 | 22.23 |
| Q | 0.118 | 0.130 | 3.00 | 3.30 |
| R | 0.390 | 0.410 | 9.91 | 10.41 |

STYLE 1:

PIN 1. COLLECTOR

2. COLLECTOR 3. BASE

4. BASE 5. EMITTER

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